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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
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09/161,196 09/25/98 HINTERMAIER

F GR-97-P-2734

LERNER AND GREENBERG
P O BOX 2480
HOLLYWOOD FL 33022-2480

MMC2/0522

EXAMINER

NGUYEN, C

ART UNIT

PAPER NUMBER

2811

DATE MAILED:

05/22/00

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Office Action Summary

Application No.

09/16/196

Applicant(s)

HINTERMAIER

Examiner

CUONG Q NGUYEN

Group Art Unit

28 11

—The MAILING DATE of this communication appears on the cover sheet beneath the correspondence address—

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE three MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, such period shall, by default, expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).

Status

- ☐ Responsive to communication(s) filed on _____.
- ☐ This action is **FINAL**.
- ☐ Since this application is in condition for allowance except for formal matters, **prosecution as to the merits is closed** in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11; 453 O.G. 213.

Disposition of Claims

- ☒ Claim(s) 1-26 is/are pending in the application.
- Of the above claim(s) 2, 4, 6, 13-24 is/are withdrawn from consideration.
- ☐ Claim(s) _____ is/are allowed.
- ☒ Claim(s) 1, 3, 5, 7-12 is/are rejected.
- ☐ Claim(s) _____ is/are objected to.
- ☐ Claim(s) _____ are subject to restriction or election requirement.

Application Papers

- ☐ See the attached Notice of Draftsperson's Patent Drawing Review, PTO-948.
- ☐ The proposed drawing correction, filed on _____ is ☐ approved ☐ disapproved.
- ☐ The drawing(s) filed on _____ is/are objected to by the Examiner.
- ☐ The specification is objected to by the Examiner.
- ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119 (a)-(d)

- ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).
 - ☐ All ☐ Some* ☐ None of the CERTIFIED copies of the priority documents have been received.
 - ☐ received in Application No. (Series Code/Serial Number) _____.
 - ☐ received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

*Certified copies not received: _____

Attachment(s)

- ☒ Information Disclosure Statement(s), PTO-1449, Paper No(s). 59
- ☒ Notice of Reference(s) Cited, PTO-892
- ☐ Notice of Draftsperson's Patent Drawing Review, PTO-948
- ☐ Interview Summary, PTO-413
- ☐ Notice of Informal Patent Application, PTO-152
- ☐ Other _____

Office Action Summary

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Drawings

3. The drawings are objected to by the PTO Draftsperson for the reasons noted on Notice of Draftsperson's Patent Drawing Review, form PTO-948 in Paper No.6.

Priority

4. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

5. The Information Disclosure Statement filed on 12-30-98 and on 1-11-00 have been considered.

Claim Rejections - 35 U.S.C. § 102

6. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

Claims 1, and 7-9 are rejected under 35 U.S.C. 102(b) as being anticipated by Summerfelt et al. (US 5,566,045).

Regarding claims 1, 7, 8, 9, Summerfelt et al. discloses a capacitor structure in an integrated semiconductor device comprising: a semiconductor substrate (30); a first electrode (34, a platinum group materials. See Summerfelt et al.'s col.10) connected to a doped region (44),

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(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371 of this title before the invention thereof by the applicant for patent.

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capacitor dielectric layer (38, a BST layer with a dielectric constant greater than 100. See Summerfelt et al.'s col.11) formed on the first electrode; a barrier layer (52, a GaP or InP layer. See Summerfelt et al.'s col.13) which is a compound of a transition element (In or Ga) and phosphorus formed below the capacitor dielectric layer formed below the capacitor dielectric layer; a second electrode formed on the capacitor dielectric layer. See Summerfelt et al.'s Fig.12.

Claims 1, 3-5, and 7-12 are rejected under 35 U.S.C. 102(a) as being anticipated by Kawakubo et al. (US 5,691,219).

Regarding claims 1, 3, 7, 8, 9, 10, 11, Kawakubo et al. discloses a capacitor structure in an integrated semiconductor device comprising: a semiconductor substrate (1) having a doped region (6b) therein; a first electrode (13, a platinum alloy) connected to the doped region through a connection structure (11, a phosphorus-doped polysilicon layer. See Kawakubo et al.'s col.7 lines 39-43); a capacitor dielectric layer (14, a BST layer with a dielectric constant greater than 100. See Kawakubo et al.'s col.8 lines 5-8) formed on the first electrode; a barrier layer (12, a layer of transition metal such as Ti or Ta. See Kawakubo et al.'s col.7 lines 55-60) formed below the capacitor dielectric layer; a second electrode (14) formed on the capacitor dielectric layer. See Kawakubo et al.'s Fig.4E.

Kawakubo et al. does not explicitly teach that the barrier is a compound of a transition element and phosphorus. It is inherent that the transition metal layer (12) will react with phosphorus from the connection structure to form a barrier material such as a TiP or TiP.

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Therefore, it is inherent that Kawakubo et al.'s device including a barrier layer of TaP or TiP. See reference US6015997 col.7 lines 55-60 which was cited to support the inherence.

Regarding claims 4-5, as shown in Fig.4E, the barrier layer is disposed directly underneath the first electrode, covers entire an interface between the first electrode and the connection structure and covers entire an interface between the first electrode and the capacitor dielectric.

Regarding claim 12, Kawakubo et al. teaches that the capacitor connected to a selection transistor through the doped region (6b). See Fig.4E.

Conclusion

7. Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

8. Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to CUONG Q NGUYEN whose telephone number is (703) 308-1293. The Examiner is in the Office generally between the hours of 6:30 AM to 5:00 PM (Eastern Standard Time) Monday through Thursday.

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9. Any inquiry of a general nature or relating to the status of this application should be directed to the Technology Center Receptionists whose telephone number is 308-0956.

CN

May 19, 2000


Minh Loan Tran
Primary Examiner